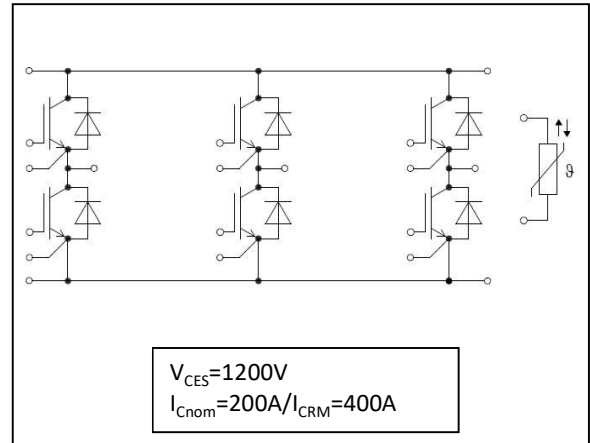


1200V 200A IGBT Full Bridge Module

1200V 200A IGBT 全桥模块



Features:

- 1200V Trench+ Field Stop technology
- Freewheeling diodes with fast and soft reverse recovery
- $V_{CE(sat)}$ with positive temperature coefficient
- Low switching losses
- Short circuit ruggedness

Typical Applications:

- Motor Drives
- Servo Drives
- Auxiliary inverters

产品特性:

- 1200V 沟槽栅+场截止技术
- 快速的软恢复特性续流二极管
- 导通压降具有正温度系数
- 低开关损耗
- 良好的短路稳定性

典型应用:

- 电机驱动器
- 伺服驱动器
- 辅助逆变器

Package / 封装

Item	Symbol	Conditions	Values	Unit
绝缘测试电压 Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, t =1 min	2.5	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘 Internal isolation		基本绝缘 (class 1, IEC 61140) Basic insulation (class 1, IEC 61140)	Al_2O_3	
爬电距离 Creepage distance	d_{Creep}	端子-散热片/terminal to heatsink	10.0	mm
电气间隙 Clearance	d_{clear}	端子-散热片/terminal to heatsink	7.5	mm
相对电痕指数 Comparative tracking index	CTI		>200	

Item	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
杂散电感, 模块 Stray inductance module	L_{SCE}			21		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C=25^{\circ}C$		1.80		$m\Omega$
储存温度 Storage temperature	T_{stg}		-40		125	$^{\circ}C$
模块安装的安装扭矩 Mounting torque for module mounting	M5		3		6	Nm
重量 Weight	G			300		g

IGBT

Maximum Rated Values / 最大额定值

Item	Symbol	Conditions	Values	Unit
集电极-发射极电压 Collector-emitter Voltage	V_{CES}	$T_{vj}=25^{\circ}C$	1200	V
栅极-发射极电压 Maximum gate-emitter voltage	V_{GES}		± 20	V
瞬态栅极-发射极电压 Transient gate-emitter voltage	V_{GES}	$t_p \leq 10\mu s, D=0.01$	± 30	V
连续集电极直流电流 Continuous DC collector current	I_C	$T_C=60^{\circ}C$	200	A
最大脉冲集电极电流 Pulsed collector current, tp limited by T_{jmax}	I_{Cpulse}		400	A
功率损耗 Power dissipation	P_{tot}		750	W

Characteristic Values / 特征值

Item	Symbol	Conditions	Values			Unit	
			Min.	Typ.	Max.		
集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200A, V_{GE}=15V$	$T_{vj}=25^{\circ}C$		1.60	2.10	V
			$T_{vj}=125^{\circ}C$		1.80		
			$T_{vj}=150^{\circ}C$		1.85		
栅极阈值电压 Gate threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}, I_C=8mA$	5.2	6.0	6.7	V	
集电极-发射极截止电流 Collector-emitter cut-off current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$	$T_{vj}=25^{\circ}C$			100	μA
			$T_{vj}=150^{\circ}C$			5	mA
栅极-发射极漏电流 Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V, T_{vj}=25^{\circ}C$	-200		200	nA	
栅极电荷 Gate Charge	Q_G	$V_{CE}=600V, I_C=200A, V_{GE}=\pm 15V$		1.6		μC	
输入电容 Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=100kHz$		24.7		nF	
输出电容 Output Capacitance	C_{oes}			0.9			
反向传输电容 Reverse Transfer Capacitance	C_{res}			0.2			
开通延迟时间 (电感负载) Turn-on delay time, inductive load	$t_{d(on)}$	$V_{CC}=600V, I_C=200A$ $R_G=3.3\Omega,$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	388		ns	
			$T_{vj}=125^{\circ}C$	428		ns	
			$T_{vj}=150^{\circ}C$	436		ns	
上升时间 (电感负载) Rise Time, inductive load	t_r	$V_{CC}=600V, I_C=200A$ $R_G=3.3\Omega,$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	44		ns	
			$T_{vj}=125^{\circ}C$	52		ns	
			$T_{vj}=150^{\circ}C$	56		ns	
关断延迟时间 (电感负载) Turn-off delay time, inductive load	$t_{d(off)}$	$V_{CC}=600V, I_C=200A$ $R_G=3.3\Omega,$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	484		ns	
			$T_{vj}=125^{\circ}C$	572		ns	
			$T_{vj}=150^{\circ}C$	588		ns	
下降时间 (电感负载) Fall time, inductive load	t_f	$V_{CC}=600V, I_C=200A$ $R_G=3.3\Omega,$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	132		ns	
			$T_{vj}=125^{\circ}C$	180		ns	
			$T_{vj}=150^{\circ}C$	196		ns	
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	E_{on}	$V_{CC}=600V, I_C=200A$ $R_G=3.3\Omega,$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	6.5		mJ	
			$T_{vj}=125^{\circ}C$	9.6		mJ	
			$T_{vj}=150^{\circ}C$	11.2		mJ	
关断损耗能量 (每脉冲) Turn off Energy loss per pulse	E_{off}	$V_{CC}=600V, I_C=200A$ $R_G=3.3\Omega,$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	11.8		mJ	
			$T_{vj}=125^{\circ}C$	16.4		mJ	
			$T_{vj}=150^{\circ}C$	17.3		mJ	
短路数据 SC data	I_{SC}	$V_{GE} \leq 15V,$ $V_{CC}=800V$	$tp \leq 10\mu s$ $T_{vj}=150^{\circ}C$		750	A	
IGBT结-外壳热阻 IGBT thermal resistance, junction-case	R_{thJC}				0.20	K/W	
工作温度 Operating Temperature	T_{Jop}		-40		150	$^{\circ}C$	

Diode / 二极管

Maximum Rated Values / 最大额定值

Item	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
反向重复峰值电压 Repetitive reverse voltage	V_{RRM}	$T_{vj}=25^{\circ}C$		1200		V
连续正向直流电流 Continuous DC forward current	I_F			200		A
二极管正向不重复峰值电流 Diode pulsed current, tp limited by T_{Jmax}	I_{Fpulse}			400		

Characteristic Values / 特征值

Item	Symbol	Conditions	Values			Unit	
			Min.	Typ.	Max.		
正向电压 Forward voltage	V_F	$I_F=200A, V_{GE}=0V$	$T_{vj}=25^{\circ}C$	1.5	1.80	2.40	V
			$T_{vj}=125^{\circ}C$		1.80		
			$T_{vj}=150^{\circ}C$		1.80		
反向恢复时间 Reverse recovery time	t_{rr}	$I_F=200A$ $di_F/dt=-6000A/\mu s$ ($T_{vj}=150^{\circ}C$)	$T_{vj}=25^{\circ}C$		864		ns
			$T_{vj}=125^{\circ}C$		1170		
			$T_{vj}=150^{\circ}C$		1280		
反向恢复峰值电流 Peak reverse recovery current	I_{RRM}	$V_R=600V,$ $V_{GE}=-15V$	$T_{vj}=25^{\circ}C$		270		A
			$T_{vj}=125^{\circ}C$		290		
			$T_{vj}=150^{\circ}C$		300		
反向恢复电荷 Reverse recovery charge	Q_{RR}		$T_{vj}=25^{\circ}C$		22.6		μC
			$T_{vj}=125^{\circ}C$		34.8		
			$T_{vj}=150^{\circ}C$		40.0		
反向恢复损耗 (每脉冲) Reverse recovery energy loss per pulse	E_{rec}		$T_{vj}=25^{\circ}C$		4.0		mJ
			$T_{vj}=125^{\circ}C$		13.7		
			$T_{vj}=150^{\circ}C$		16.1		
二极管结-外壳热阻 Diode thermal resistance, junction-case	R_{thJC}				0.30	K/W	
工作温度 Operating Temperature	T_{Jop}		-40		150	$^{\circ}C$	

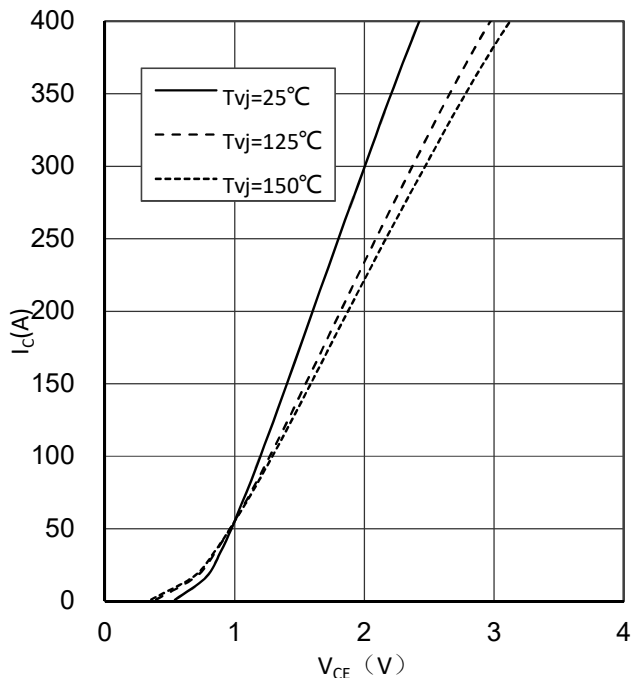
NTC-Thermistor / 负温度系数热敏电阻

Characteristic Values / 特征值

Item	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
额定电阻值 Rated resistance	R_{25}	$T_C=25^{\circ}C$		5.00		k Ω
B-值 B-value	$R_{25/50}$			3375		K

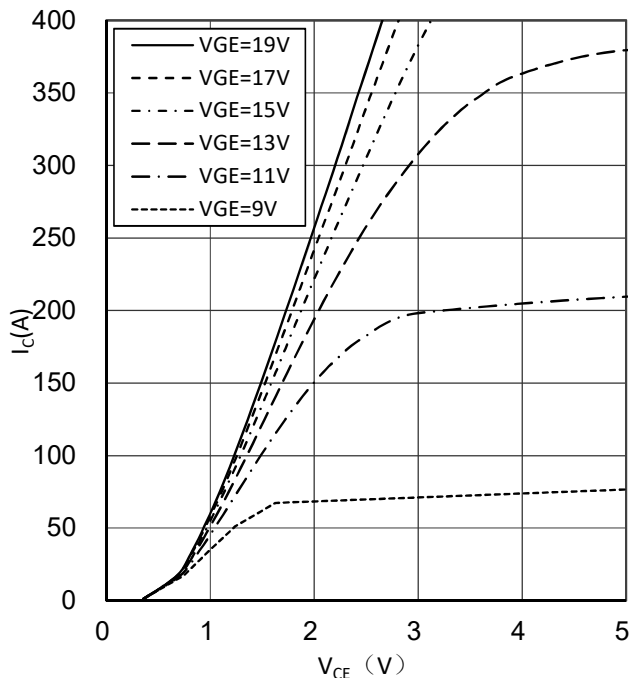
输出特性 (典型)
Output characteristic (typical)

$I_C = f(V_{CE})$



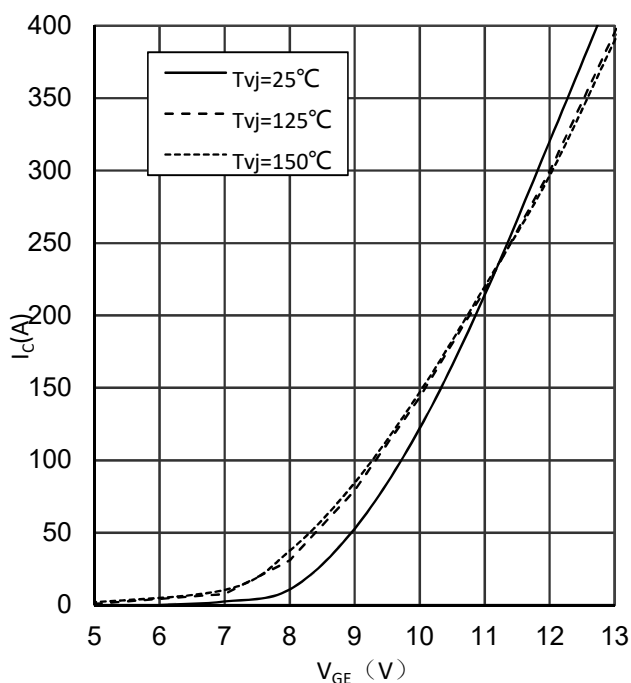
输出特性 (典型)
Output characteristic (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



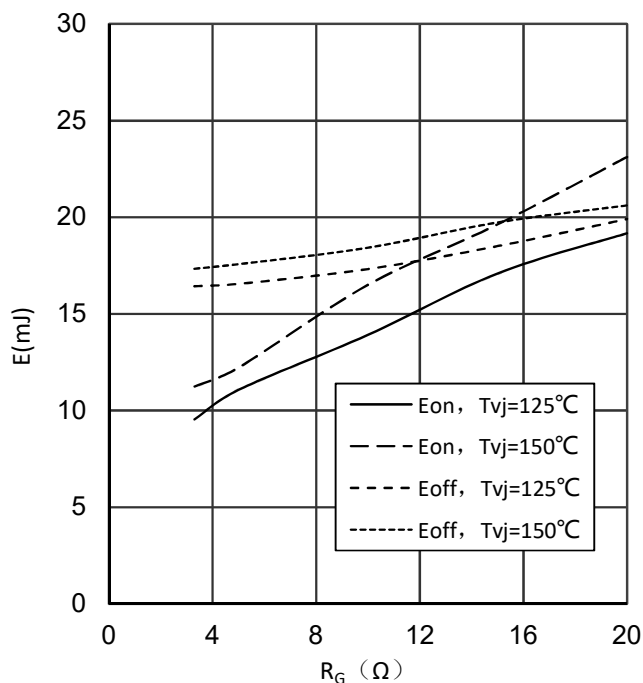
传输特性 (典型)
Transfer characteristic (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{V}$



IGBT开关损耗 (典型)
Switching losses IGBT (typical)

$E = f(R_G)$
 $V_{GE} = \pm 15\text{V}, I_C = 200\text{A}, V_{CE} = 600\text{V}$

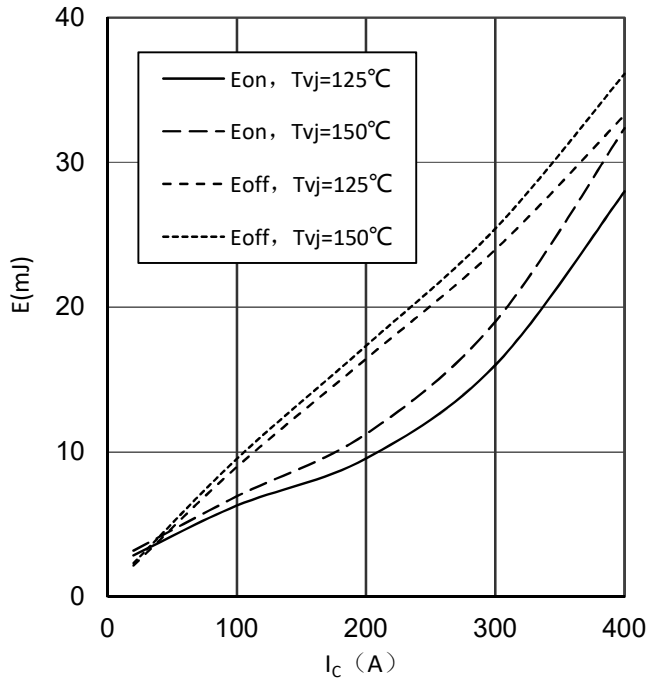


IGBT开关损耗 (典型)

Switching losses IGBT (typical)

$E = f(I_c)$

$V_{GE} = \pm 15V, R_G = 3.3\Omega, V_{CE} = 600V$

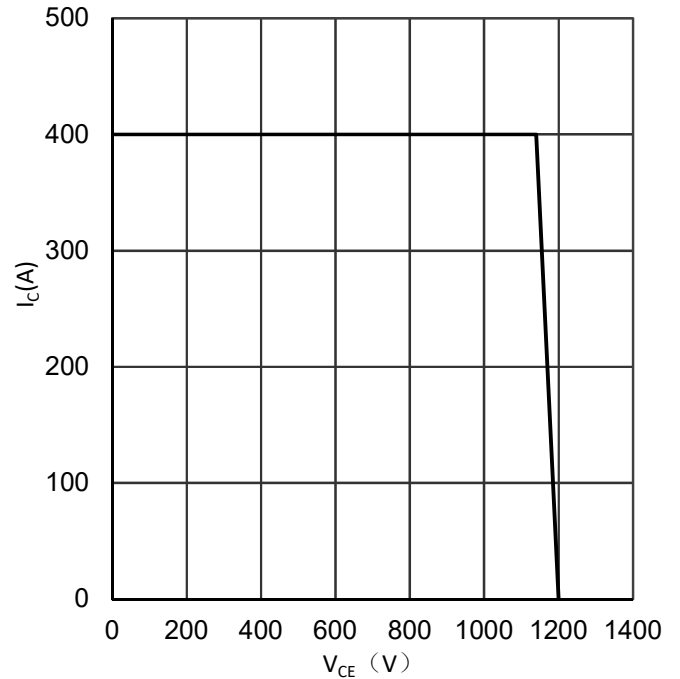


反偏安全工作区 (RBSOA)

Reverse bias safe operating area(RBSOA)

$I_c = f(V_{CE})$

$V_{GE} = \pm 15V, R_{goff} = 3.3\Omega, T_{vj} = 150^\circ C$

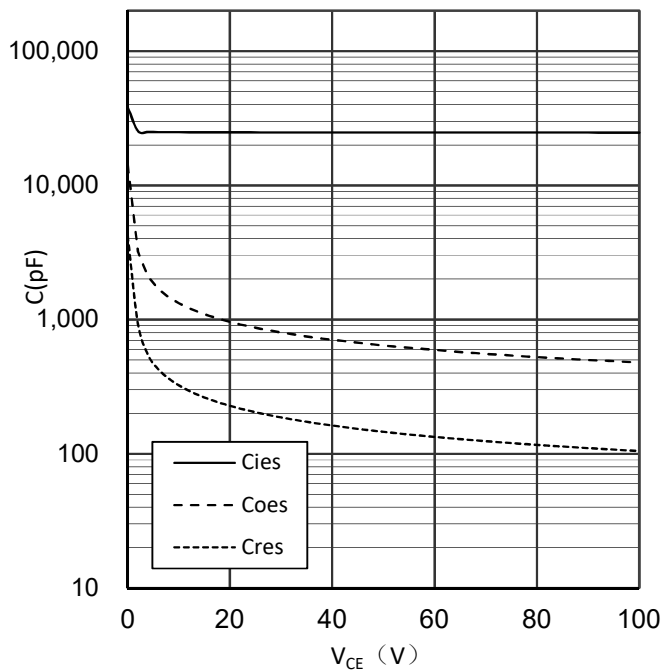


电容 (典型)

Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

$f = 100\text{ kHz}, V_{GE} = 0V$

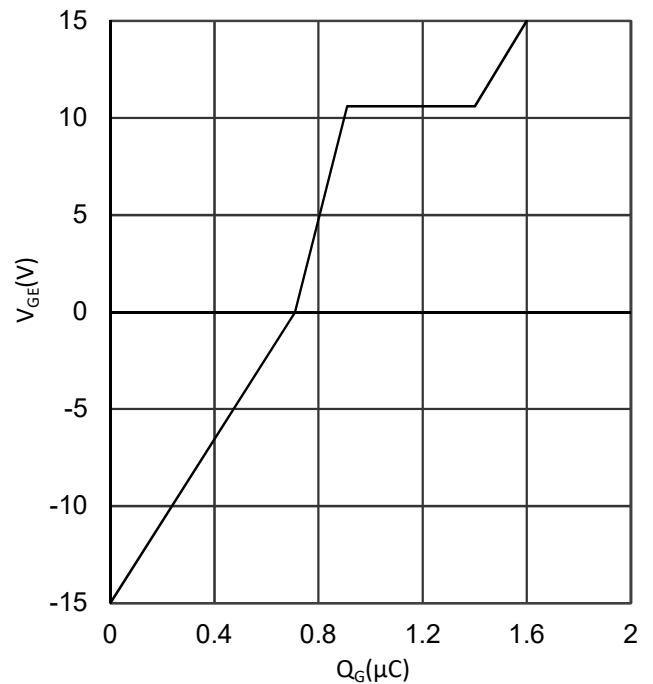


门极电荷 (典型)

Gate charge (typical)

$V_{GE} = f(Q_G)$

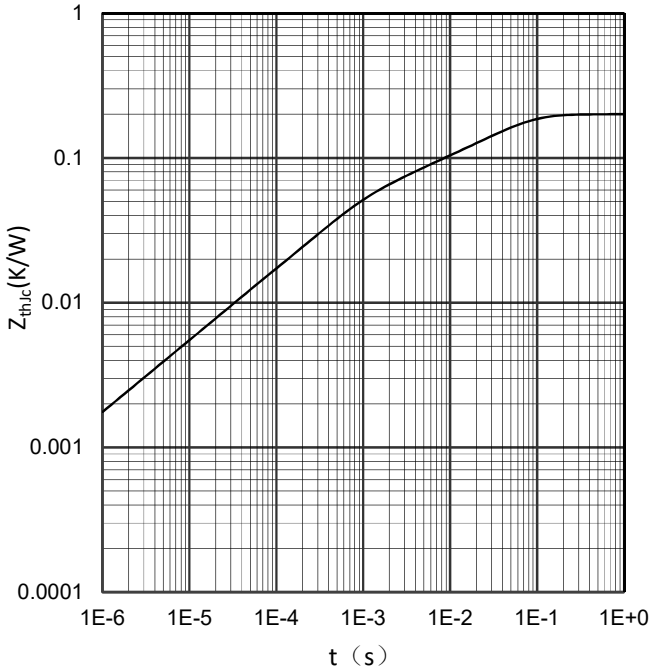
$I_c = 200A, V_{CE} = 600V$



IGBT瞬态热阻抗

IGBT transient thermal impedance as a function of pulse width

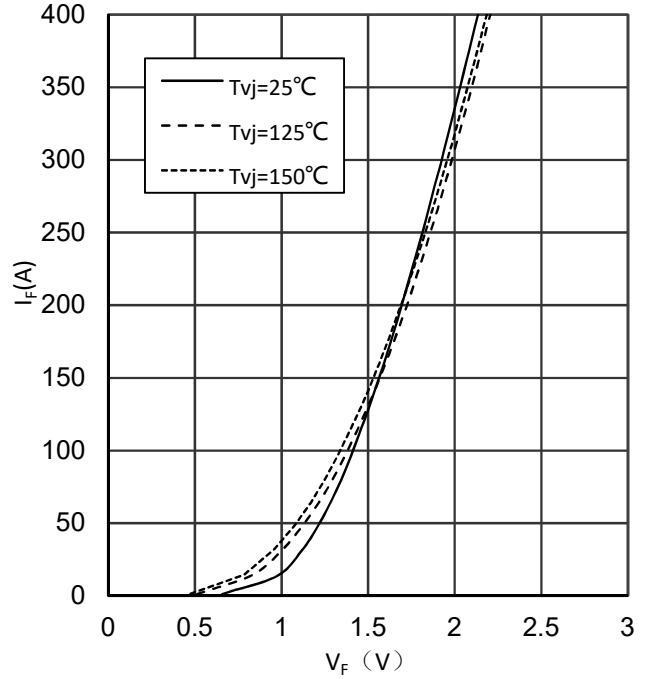
$$Z_{th(j-c)} = f(t)$$



正向偏压特性 二极管 (典型)

Forward characteristic of Diode (typical)

$$I_F = f(V_F)$$

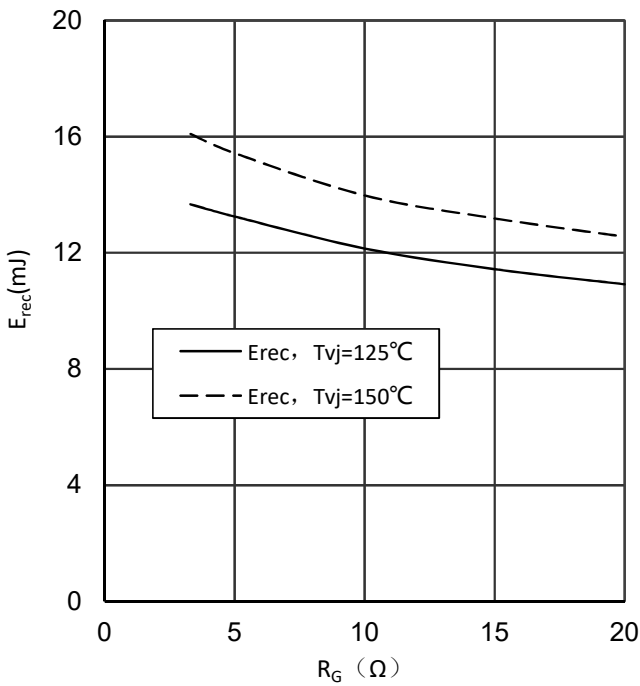


开关损耗 二极管 (典型)

Switching losses Diode (typical)

$$E_{rec} = f(R_G)$$

$I_F = 200A, V_{CE} = 600V$

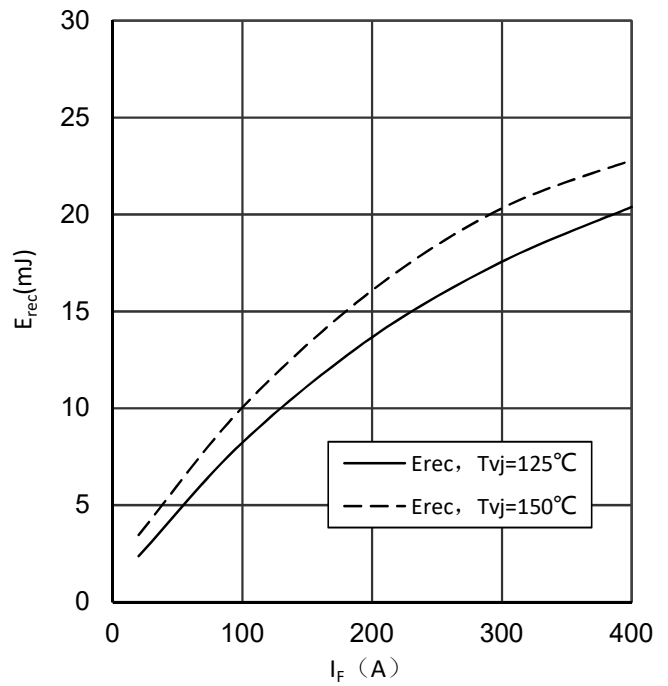


开关损耗 二极管 (典型)

Switching losses Diode (typical)

$$E_{rec} = f(I_F)$$

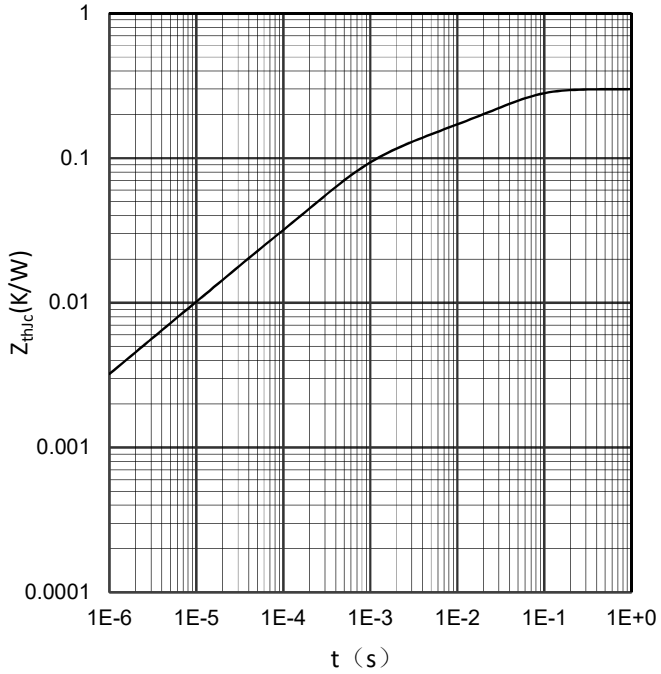
$R_G = 3.3Ω, V_{CE} = 600V$



二极管瞬态热阻抗

Diode transient thermal impedance as a function of pulse width

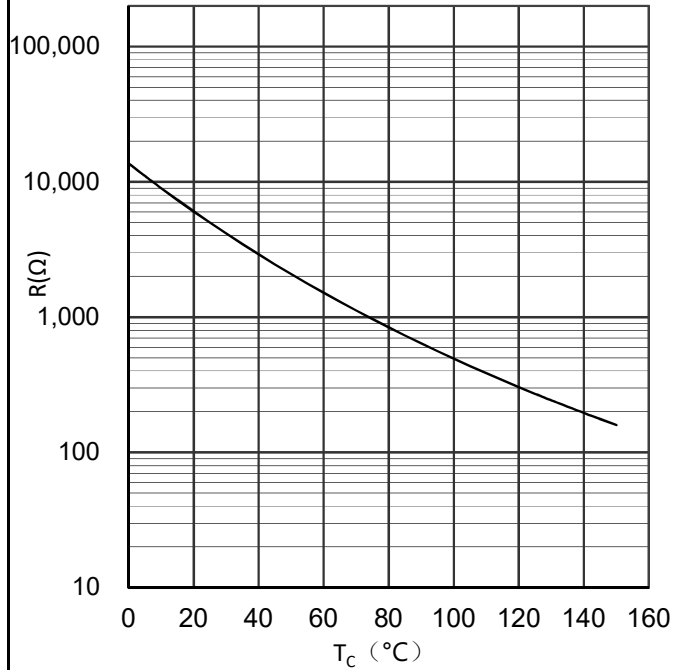
$$Z_{th(j-c)} = f(t)$$



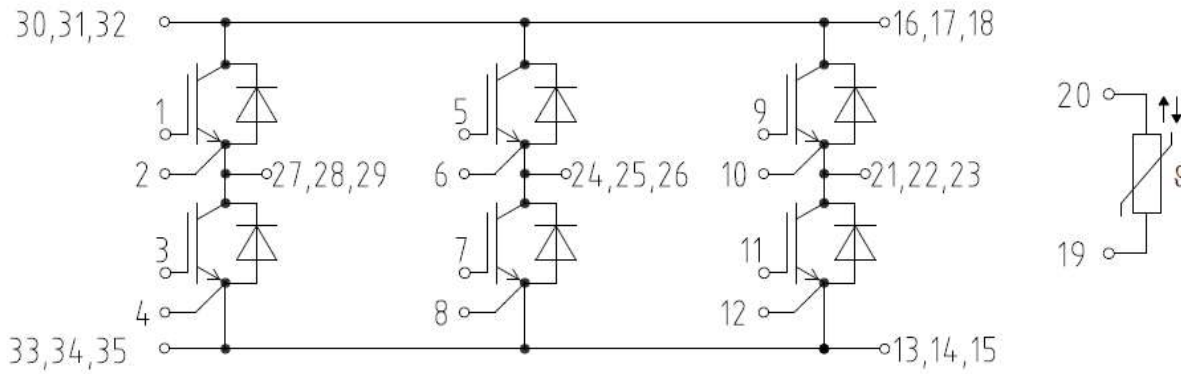
热敏电阻温度特性 (典型)

NTC-Thermistor-temperature characteristic (typical)

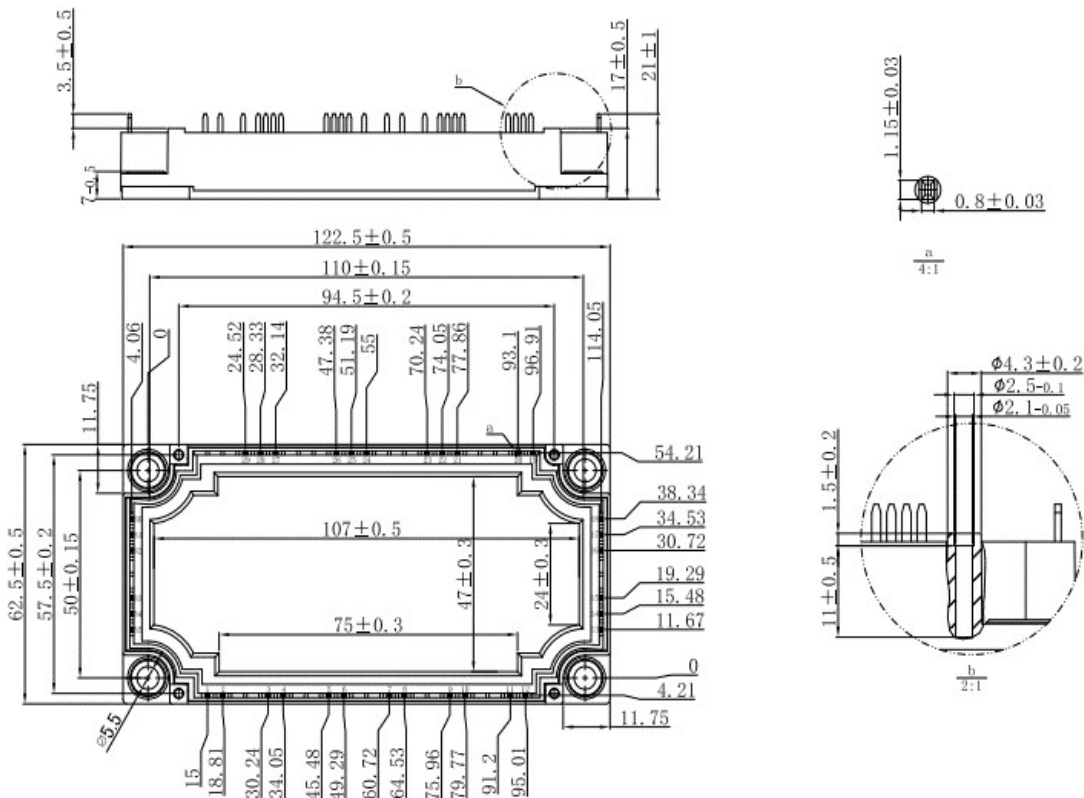
$$R = f(T)$$



Circuit diagram headline / 接线图



Package outlines / 封装尺寸



Dimensions in (mm)
单位: mm